

ABSTRACT OF THE DISCLOSURE

The present invention provides a manufacturing method that allows a Group III nitride substrate with a low dislocation density to be
5 manufactured, and a semiconductor device that is manufactured using the manufacturing method. The manufacturing method includes, in an atmosphere including nitrogen, allowing a Group III element and the nitrogen to react with each other in an alkali metal melt to cause generation and growth of Group III nitride crystals. In the manufacturing method, a
10 plurality of portions of a Group III nitride semiconductor layer are prepared, selected as seed crystals, and used for at least one of the generation and the growth of the Group III nitride crystals, and then surfaces of the seed crystals are brought into contact with the alkali metal melt.